16V Low Cost, High Performance CMOS Rail-to-Rail Operational Amplifiers

Preliminary Technical Data

AD8661/AD8662/AD8664

FEATURES
Low Offset Voltage: 75 μV max
Low Input Bias Currents 1pA Max
Single-Supply Operation: 5 to 16 Volts
Dual-Supply Operation: +/- 2.5 to +/-8 Volts
Low Noise: 10 nV/√Hz
Wide Bandwidth: 4 MHz
Unity Gain Stable

APPLICATIONS
Multi-pole Filters
Sensors
Medical Equipment
Consumer Audio
Photodiode amplification
ADC driver

GENERAL DESCRIPTION

The AD8661, AD8662 and AD8664 are single, dual and quad rail-to-rail output single supply amplifiers that use Analog Devices' patented DigiTrim® trimming technique to achieve low offset voltage. The AD8661 family features an extended operating range with supply voltages up to 16 V. They also feature low input bias currents, wide signal bandwidth, and low input voltage and current noise.

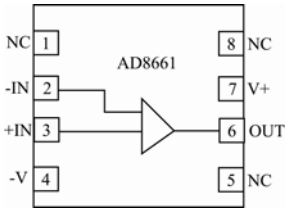
The combination of low offsets, very low input bias currents, and wide supply range make these amplifiers useful in a wide variety of applications normally associated with much higher priced JFET amplifiers. Systems utilizing high impedance sensors, such as photo-diodes benefit from the combination of low input bias current, low noise, low offset and bandwidth. The wide operating voltage range matches today's high performance ADCs and DACs. Audio applications and medical monitoring equipment can take advantage of the high input impedance, low voltage and current noise, wide bandwidth and the lack of "popcorn" noise (found in many other low input bias current amplifiers).

The AD8661, AD8662 and AD8664 are specified over the extended industrial (-40° to +125°C) temperature range. The AD8661, single, is available in the tiny 8-lead LFCSP (MO-220) 3mm x 3mm and 8-lead SOIC package. The AD8662, dual, is available in the 8-lead micro-SOIC and narrow SOIC surface mount packages. The AD8664, quad, is available in 14-lead TSSOP and narrow 14-pin SOIC packages.

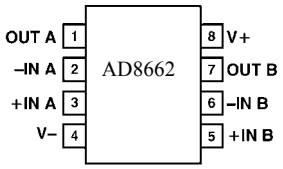
LFCSP, MSOP and TSSOP versions are available in tape and reel only.

PIN CONFIGURATIONS

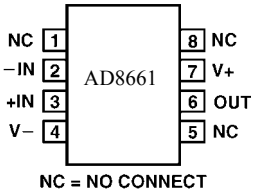
8-Lead LFCSP (CP-8) 3mm x 3mm



8-Lead MSOP (RM-8)

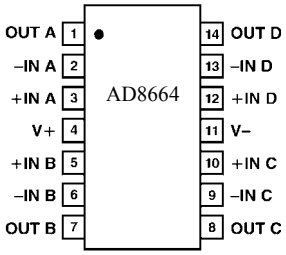


8-Lead SO (R-8)



NC = NO CONNECT

14-Lead TSSOP (RU-14)



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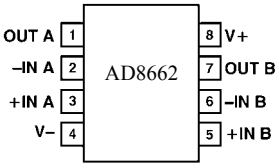
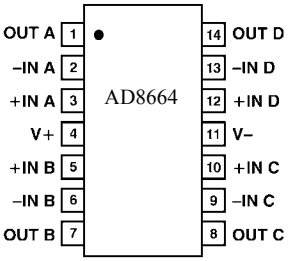


14-Lead SO (R-14)



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One Technology Way, P.O. Box 9106, Norwood, MA 02062-9106, U.S.A.
Tel: 781/329-4700 **www.analog.com**
Fax: 781/326-8703

ELECTRICAL CHARACTERISTICS (V_S=+5.0V, V_{CM} = V_S/2, T_A=+25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
INPUT CHARACTERISTICS						
Offset Voltage	V_{OS}	V_{SY} = 8V, V_{CM} = 3V			75	μV
		V_{CM} = 0.1V to 3.0V		30	300	μV
		-40°< T_A < +85°C			650	μV
		-40°< T_A < +125°C			750	μV
Input Bias Current	I_B			0.3	1	pA
		-40°< T_A < +85°C			50	pA
		-40°< T_A < +125°C			300	pA
Input Offset Current	I_{OS}			0.2	TBD	pA
		-40°< T_A < +85°C			20	pA
		-40°< T_A < +125°C			75	pA
Input Voltage Range			tbd		3.0	V
Common-Mode Rejection Ratio	CMRR	V_{CM} = 0.1V to 3.0V	80	95		dB
Large Signal Voltage Gain	A_{VO}	R_L = 10 kΩ V_O= 0.5V to 4.5V	70	100		V/mV
Offset Voltage Drift	$\Delta V_{OS}/\Delta T$			3	10	μV/°C
OUTPUT CHARACTERISTICS						
Output Voltage High	V_{OH}	I_L = 1mA	4.80	4.85		V
		I_L = 10mA	4.80	4.85		V
		-40°C < T_A < +125°C	4.75			V
Output Voltage Low	V_{OL}	I_L = 1mA		60	120	mV
	V_{OL}	I_L = 1mA		60	120	mV
		-40°C < T_A < +125°C			150	mV
Output Current	I_{OUT}			±19		mA
Closed Loop Output Impedance	Z_{OUT}	f=1 MHz, A_V = 1		65		Ω
POWER SUPPLY						
Power Supply Rejection Ratio	PSRR	V_S = 5 V to 16 V	80	95		dB
Supply Current/Amplifier	I_{SY}	V_O = 0V		1.2	1.8	mA
		-40°< T_A < +125°C			2.0	mA
DYNAMIC PERFORMANCE						
Slew Rate	SR	R_L =10 kΩ		3		V/μs
Settling Time	t_s	To 0.1%, 0 V to 1V step		<1		μs
Gain Bandwidth Product	GBP			4		MHz
Phase Margin	Øo degrees	C_L = 15 pF			60	
NOISE PERFORMANCE						
Peak-to-Peak Noise	e_n p-p	f=0.1Hz to 10 Hz		2.5		μV p-p
Voltage Noise Density	e_n	f=1kHz		12		nV/√Hz
Voltage Noise Density	e_n	f=10kHz		10		nV/√Hz
Current Noise Density	i_n	f=1kHz		0.1		pA/√Hz

ELECTRICAL CHARACTERISTICS (V_S=±8.0V, V_{CM} = 0, T_A=+25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
INPUT CHARACTERISTICS						
Offset Voltage	V_{OS}	V_{SY} = 8V, V_{CM} = 3V			75	μV
		V_{CM} = -8.1V to +6.0V		30	300	μV
		-40°< T_A < +85°C			650	μV
		-40°< T_A < +125°C			750	μV
Input Bias Current	I_B			0.3	1	pA
		-40°< T_A < +85°C			50	pA
		-40°< T_A < +125°C			300	pA
Input Offset Current	I_{OS}			0.2	TBD	pA
		-40°< T_A < +85°C			20	pA
		-40°< T_A < +125°C			75	pA
Input Voltage Range			tbd		6	V
Common-Mode Rejection Ratio	CMRR	V_{CM} = -8.1V to +6.0V	80	95		dB
Large Signal Voltage Gain	A_{VO}	R_L=10 kΩ V_O= -7.5V to+7.5V	70	85		V/mV
Offset Voltage Drift	$\Delta V_{OS}/\Delta T$			3	10	μV/°C
OUTPUT CHARACTERISTICS						
Output Voltage High	V_{OH}	I_L = 1mA	7.90	7.95		V
		I_L = 10mA	7.6	7.7		V
		-40°C < T_A < +125°C	7.4			V
Output Voltage Low	V_{OL}	I_L = 1mA		-7.97	-7.93	mV
		I_L = 10mA		-7.8	-7.7	mV
		-40°C < T_A < +125°C			-7.5	mV
Output Current	I_{OUT}			±140		mA
Closed Loop Output Impedance	Z_{OUT}	f=1 MHz, A_V = 1		45		Ω
POWER SUPPLY						
Power Supply Rejection Ratio	PSRR	V_S = 5V to 16V	80	95		dB
Supply Current/Amplifier	I_{SY}	V_O = 0V		1.5	1.8	mA
		-40°< T_A < +125°C			2.0	mA
DYNAMIC PERFORMANCE						
Slew Rate	SR	R_L =10 kΩ		3		V/μs
Settling Time	t_s	To 0.1%, 0 V to 1V step		<1		μs
Gain Bandwidth Product	GBP			4		MHz
Phase Margin	Øo	C_L = 15 pF		60		degrees
NOISE PERFORMANCE						
Peak-to-Peak Noise	e_n p-p	f=0.1Hz to 10 Hz		2.5		μV p-p
Voltage Noise Density	e_n	f=1kHz		12		nV/√Hz
Voltage Noise Density	e_n	f=10kHz		10		nV/√Hz
Current Noise Density	i_n	f=1kHz		0.1		pA/√Hz

ABSOLUTE MAXIMUM RATINGS[1]

Supply voltage ..... +18V
Input Voltage ..... Gnd to Vs
Differential Input Voltage ..... ±18V
Output Short-Circuit Duration to Gnd[2] ..... Observe Derating Curves
Storage Temperature Range
R, CP, RM, RU Package ..... -65°C to +150°C
Operating Temperature Range
AD8661/AD8662/AD8664 ..... -40°C to +125°C
Junction Temperature Range
R, CP, RM, RU Package ..... -65°C to +150°C
Lead Temperature Range (Soldering, 60 Sec) ..... +300°C

Package Type	θ_{JA}	θ_{JC}	Units
8-Pin LFCSP (CP)		--	°C/W
8-Pin microSOIC (RM)	210	45	°C/W
8-Pin SOIC (R)	158	43	°C/W
14-Pin SOIC (R)	120	36	°C/W
14-Pin TSSOP (RU)	180	35	°C/W

NOTES

[1] Absolute maximum ratings apply at 25°C, unless otherwise noted.

[2] θ_{JA} is specified for the worst-case conditions, i.e., θ_{JA} is specified for device soldered in circuit board for surface mount packages.

ORDERING GUIDE

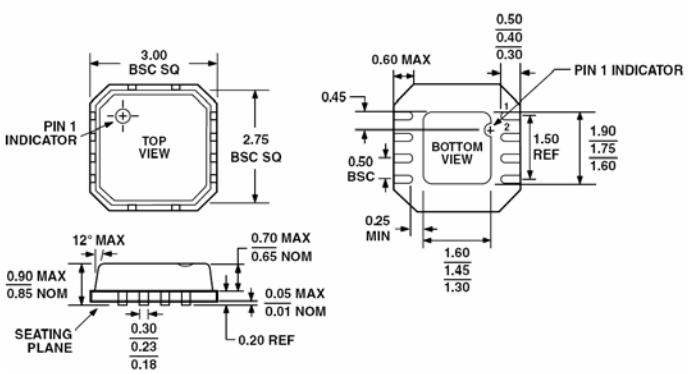
Model	Temperature Range	Package Description	Package Option	Branding Information
AD8661ACP	-40°C to +125°C	8-Pin LFCSP	CP-8	
AD8661ARZ	-40°C to +125°C	8-Pin SOIC	R-8	
AD8662ARMZ	-40°C to +125°C	8-Pin micro-SOIC	RM-8	
AD8662ARZ	-40°C to +125°C	8-Pin SOIC	R-8	
AD8664ARZ	-40°C to +125°C	14-Pin SOIC	R-14	
AD8664ARUZ	-40°C to +125°C	14-Pin TSSOP	RU-14	

CAUTION

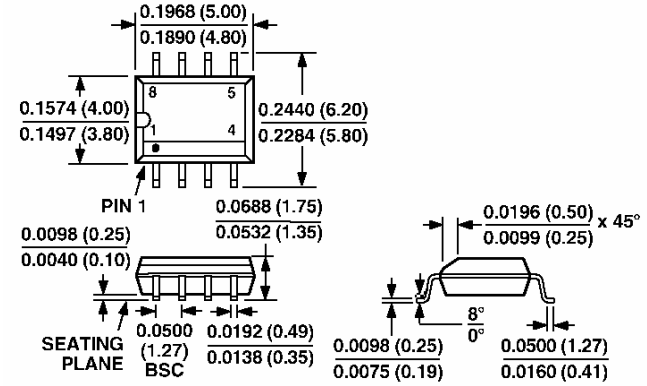
ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 1500 V readily accumulate on the human body and test equipment and can discharge without detection. Although this device features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high-energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.

OUTLINE DIMENSIONS

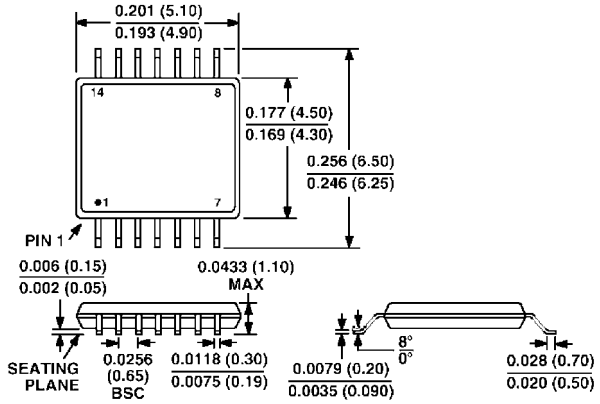
8-Lead LFCSP (CP-8 Suffix)



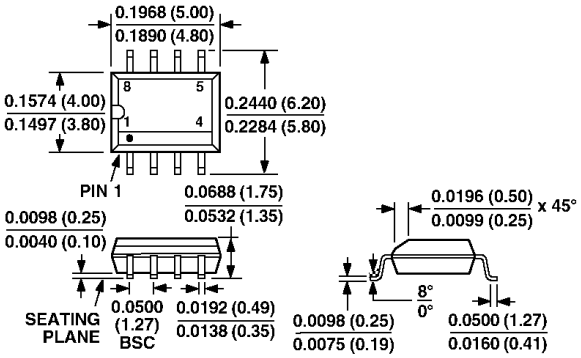
8-Lead SOIC (RM-8)



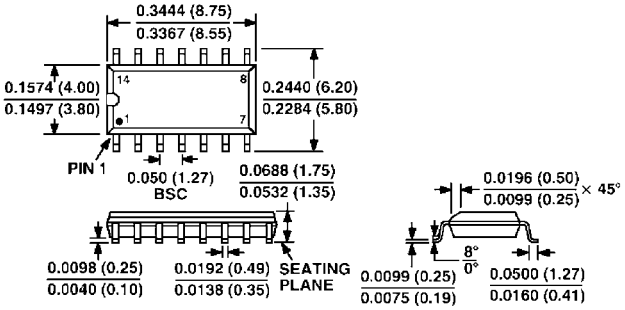
14-Lead TSSOP (RU-14)



8-Lead SO (R-8)



14-Lead SO (R-14)



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